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Manufacturers of World Class Discrete Semiconductors

CMPFJ310

SURFACE MOUNT
SILICON N-CHANNEL JFET

SOT-23 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPFJ310 type is a epoxy molded N-Channel Silicon Junction Field Effect Transistor manufactured in an SOT-23 case, designed for VHF/UHF amplifier applications.
Marking code is 6T.

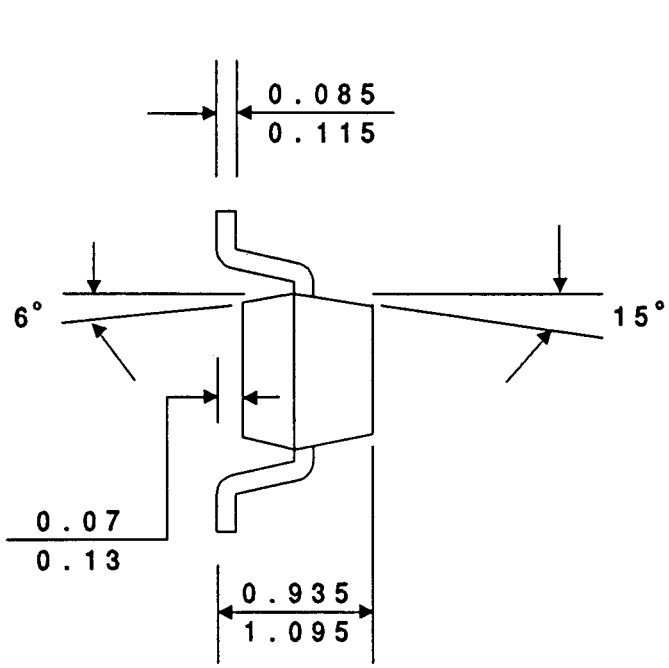
MAXIMUM RATINGS ($T_A = 25^oC$)

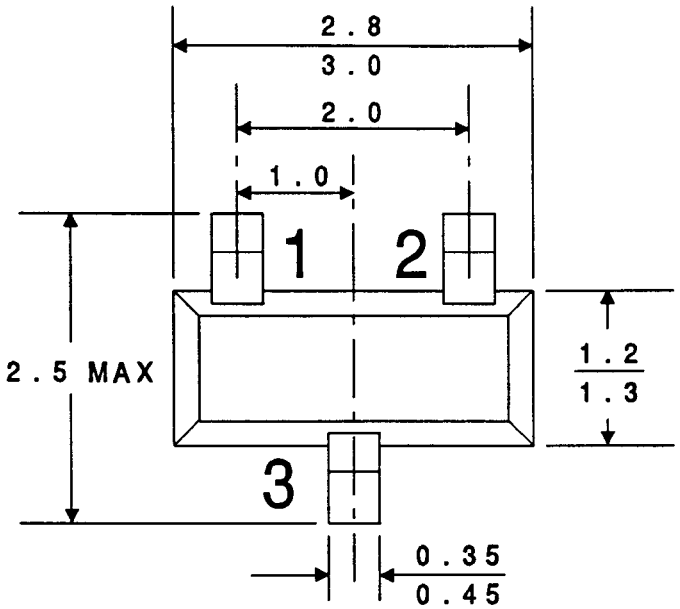
	SYMBOL		UNITS
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	25	V
Gate Current	I_G	10	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	^oC
Thermal Resistance	Θ_{JA}	357	$^oC/W$

ELECTRICAL CHARACTERISTICS ($T_A = 25^oC$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSS}	$V_{GS} = 15V$			1.0	nA
I_{GSS}	$V_{GS} = 15V$, $T_A = 125^oC$			1.0	μA
I_{DSS}	$V_{DS} = 10V$, $V_{GS} = 0$	24		60	mA
BV_{GSS}	$I_G = 1.0\mu A$	25			V
$V_{GS(off)}$	$V_{DS} = 10V$, $I_D = 1.0nA$	2.0		6.5	V
$V_{GS(f)}$	$I_G = 1.0mA$, $V_{DS} = 0$			1.0	V
$\|Y_{fs}\|$	$V_{DS} = 10V$, $I_D = 10mA$, $f = 1.0kHz$	8.0		18	mmhos
$\|y_{os}\|$	$V_{DS} = 10V$, $I_D = 10mA$, $f = 1.0kHz$			250	μmhos
C_{iss}	$V_{GS} = 10V$, $V_{DS} = 0$, $f = 1.0MHz$			5.0	pF
C_{rss}	$V_{GS} = 10V$, $V_{DS} = 0$, $f = 1.0MHz$			2.5	pF
$\bar{e}_n$	$V_{DS} = 10V$, $I_D = 10mA$, $f = 100Hz$		10		$nV/\sqrt{Hz}$

All Dimensions in mm.





LEAD CODE:

1) SOURCE
2) DRAIN
3) GATE

MARKING CODE: 6T